



P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 20	0.0073 at $V_{GS} = -4.5 \text{ V}$	- 20		
	0.0090 at V _{GS} = - 2.5 V	- 18		
	0.013 at V _{GS} = - 1.8 V	- 15		

PowerPAK SO-8

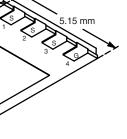
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFETs
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile



APPLICATIONS

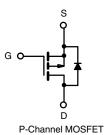
· Battery Switch for Portable Devices



Bottom View

Ordering Information: Si7485DP-T1-E3 (Lead (Pb)-free)

Si7485DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Proin Current /T = 150 °C\8	T _A = 25 °C	I _D	- 20	- 12.5	Δ.
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 16.5	- 9.5	
Pulsed Drain Current		I _{DM}	- 50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 4.5	- 1.6	
Marian and Danier Dissipation a	T _A = 25 °C	- P _D	5	1.8	W
Maximum Power Dissipation ^a	T _A = 70 °C		3.2	1.1	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b,c}		•	260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian de Ambienta	t ≤ 10 s	R _{thJA}	20	25	°C/W
Maximum Junction-to-Ambient ^a	Steady State		54	68	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.7	2.2	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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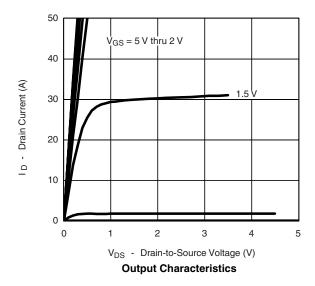
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Condition		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -1$ mA	- 0.4		- 0.9	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zone Ooks Walks as Durin Orangel	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1			
Zero Gate Voltage Drain Current		V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 70 °C			- 10	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 40			Α		
		V _{GS} = - 4.5 V, I _D = - 20 A		0.006	0.0073	Ω		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 18 A		0.0074	0.0090			
		V _{GS} = - 1.8 V, I _D = - 15 A		0.0106	0.013			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 20 A		80		S		
Diode Forward Voltage ^a	V_{SD}	I _S = - 4.5 A, V _{GS} = 0 V		- 0.62	- 1.1	V		
Dynamic ^b								
Total Gate Charge	Q_g			99	150			
Gate-Source Charge	Q_{gs}	V _{DS} = - 10 V, V _{GS} = - 5 V, I _D = - 20 A		11.5		nC		
Gate-Drain Charge	Q_{gd}			29				
Gate Resistance	R_{g}			2.4		Ω		
Turn-On Delay Time	t _{d(on)}			80	120			
Rise Time	t _r	$ \begin{array}{c c} \hline t_r & V_{DD} = \text{- 10 V, R}_L = \text{10 } \Omega \\ \hline t_{d(off)} & I_D \cong \text{- 1 A, V}_{GEN} = \text{- 4.5 V, R}_g = \text{6 } \Omega \\ \hline \end{array} $		140	210	ns		
Turn-Off Delay Time	t _{d(off)}			360	540			
Fall Time	t _f			170	260			
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -2.9 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		55	80			

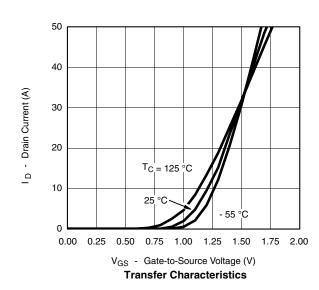
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



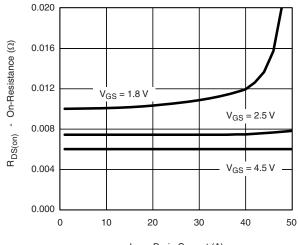


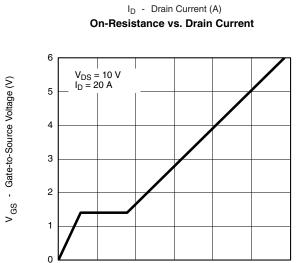






TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





60

Q_g - Total Gate Charge (nC)

Gate Charge

80

100

120

20

0

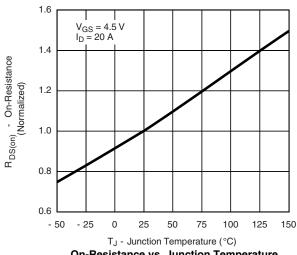
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T_J = 150 °C 10 - Source Current (A) T_J = 25 °C 0.1 0.0 0.2 0.4 0.6 0.8 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V)

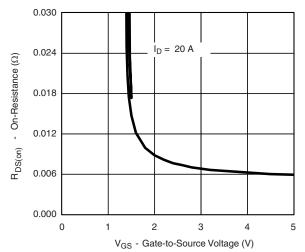
Source-Drain Diode Forward Voltage

11000 8800 C - Capacitance (pF) C_{iss} 6600 4400 2200 C_{rss} 0 0 12 16 20

V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature

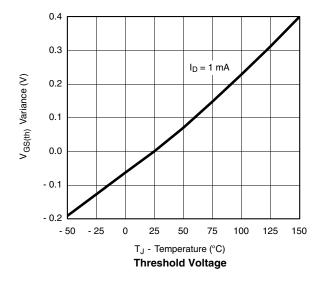


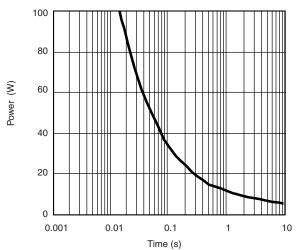
On-Resistance vs. Gate-to-Source Voltage

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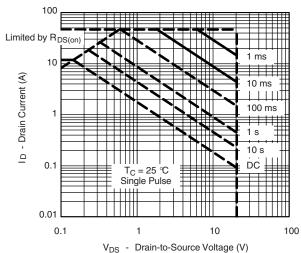
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

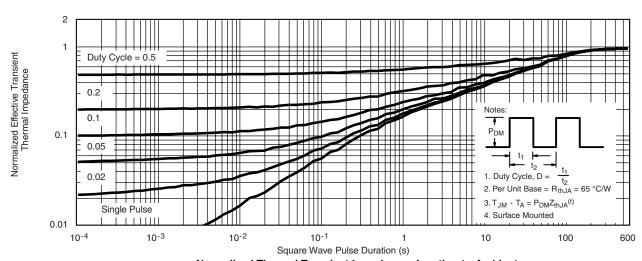




Single Pulse Power, Junction-to-Ambient



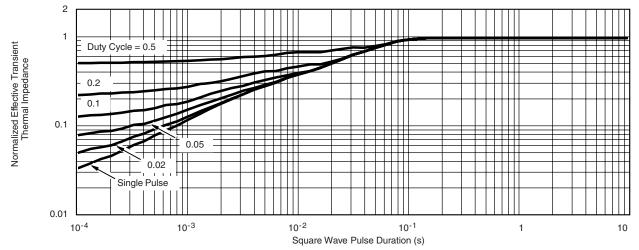
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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